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Amendment RP 8-26-02

Attorney's Docket No. 33277-004

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Patent Application of)

Nadim HADDAD et al)

Application No.: 09/629,172)

Filed: July 31, 2000)

For: METHOD TO HARDEN SHALLOW)
TRENCH ISOLATION AGAINST)
TOTAL IONIZING DOSE RADIATION)

Group Art Unit: 2812

Examiner: R. Pompey

#11/Amend
8/1/02
8-27-02

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20231.

AMENDMENT AFTER FINAL REJECTION

Richard J. McGrath
(Type or print name of person making paper or fee)
(Signature of person making paper or fee)

Assistant Commissioner for Patents
Washington, D.C. 20231

Sir:

In response to the Office Action dated February 26, 2002, please amend the above-identified patent application as follows:

IN THE CLAIMS:

Please cancel claims 5 and 7 and substitute twice amended claim 1 as follows:

1. (Twice Amended) A method for fabricating radiation-tolerant integrated circuit devices, said method comprising:

depositing a layer of pad oxide on a semiconductor substrate;

selectively etching said pad oxide layer and said semiconductor substrate to define a trench within said semiconductor substrate;

implanting boron ions at an angle with respect to normal in said trench;

implanting a p-type material to form a P-well having a depth greater than the depth of the trench; and

D/C
cont

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